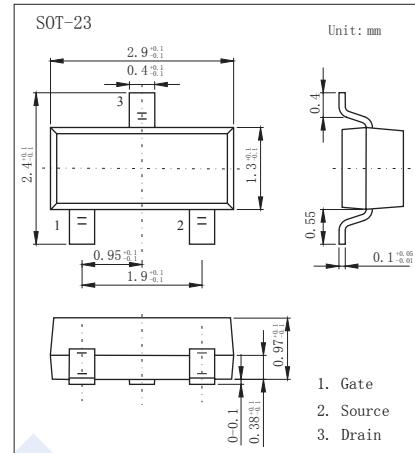
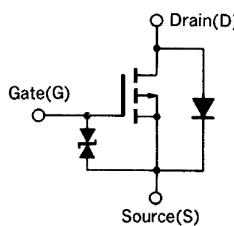


## P-Channel MOSFET

### 2SJ185

#### ■ Features

- $V_{DS} (V) = -50V$
- $I_D = -0.1 A (V_{GS} = -4V)$
- $R_{DS(ON)} < 20 \Omega (V_{GS} = -4V)$
- $R_{DS(ON)} < 40 \Omega (V_{GS} = -2.5V)$
- Complementary to 2SK1399



#### ■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	-50	V
Gate-Source Voltage	$V_{GS}$	$\pm 7$	
Continuous Drain Current	$I_D$	-100	mA
Pulsed Drain Current (Note.1)	$I_{DM}$	-200	
Power Dissipation	$P_D$	200	mW
Junction Temperature	$T_J$	150	$^\circ C$
Operating Temperature	$T_{opt}$	-55 to 80	
Junction Storage Temperature Range	$T_{stg}$	-55 to 150	

Note.1:  $PW \leq 10ms$ , Duty Cycle  $\leq 50\%$

#### ■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{DSS}$	$I_D = -250 \mu A, V_{GS} = 0V$	-50			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -50V, V_{GS} = 0V$			-10	$\mu A$
Gate-Body leakage current	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 7V$			$\pm 5$	$\mu A$
Gate Cut off Voltage	$V_{GS(off)}$	$V_{DS} = -3V, I_D = -1\mu A$	-1.2		-2	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -2.5V, I_D = -1mA$			40	$\Omega$
		$V_{GS} = -4V, I_D = -10mA$			20	
Forward Transconductance	$g_{FS}$	$V_{DS} = -3V, I_D = -10mA$	20	42		$mS$
Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = -3V, f = 1MHz$		22		$pF$
Output Capacitance	$C_{oss}$			12		
Reverse Transfer Capacitance	$C_{rss}$			4		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS(on)} = -3V, V_{DS} = -3V, I_D = -20mA, R_L = 150 \Omega, R_{GEN} = 10 \Omega$		80		$ns$
Turn-On Rise Time	$t_r$			230		
Turn-Off Delay Time	$t_{d(off)}$			40		
Turn-Off Fall Time	$t_f$			70		

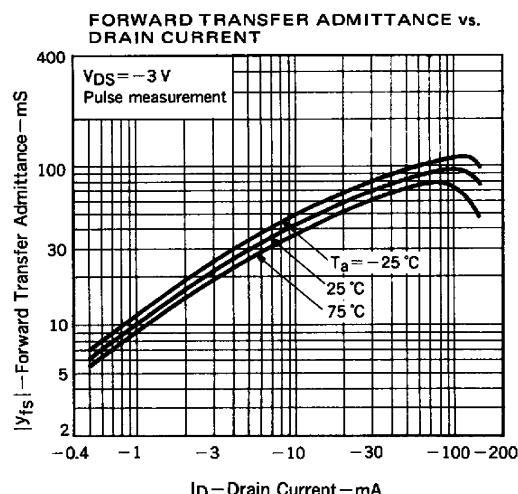
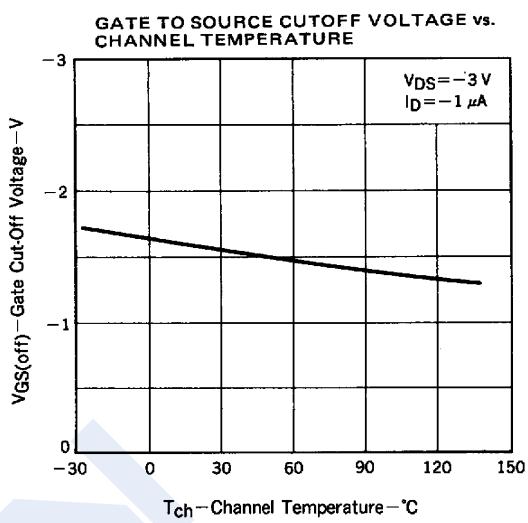
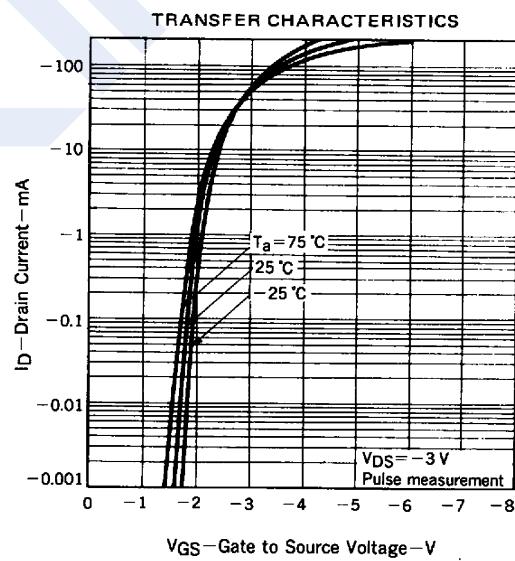
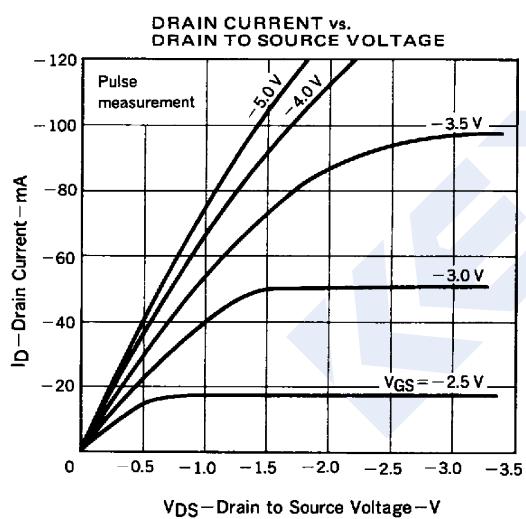
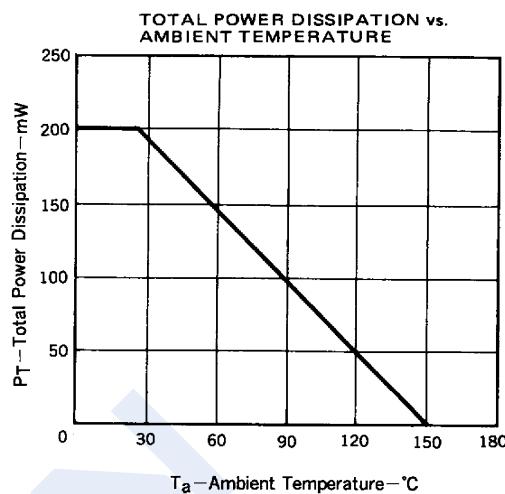
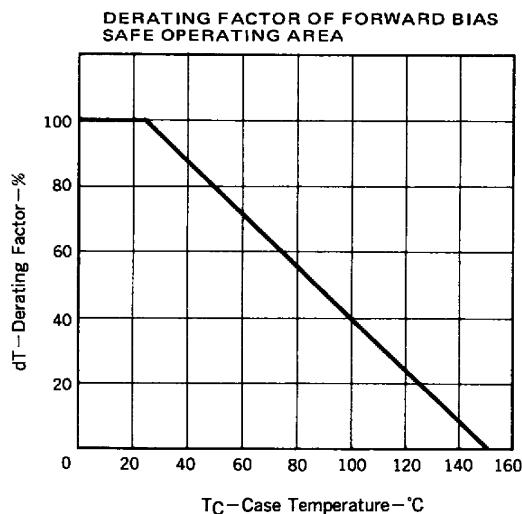
#### ■ Marking

Marking	H12
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## P-Channel MOSFET

### 2SJ185

#### ■ Typical Characteristics



## P-Channel MOSFET

### 2SJ185

#### ■ Typical Characteristics

